## 1. General description

PNP high-voltage low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a SOT223 (SC-73) medium power Surface-Mounted Device (SMD) plastic package.

NPN complement: PBHV8115Z-Q

#### 2. Features and benefits

- · High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain h<sub>FE</sub> at high I<sub>C</sub>
- Medium power SMD plastic package
- Qualified according to AEC-Q101 and recommended for use in automotive applications

## 3. Applications

- LED driver for LED chain module
- LCD backlighting
- · High Intensity Discharge (HID) front lighting
- Automotive motor management
- · Hook switch for wired telecom
- Switch mode power supply

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-150	V
Ic	collector current		-	-	-1	Α
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -10 V; $I_{C}$ = -50 mA; $T_{amb}$ = 25 °C	100	220	-	

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	C
2	С	collector		В
3	Е	emitter		
4	С	collector	<b>∃</b> 1 <b>∃</b> 2 <b>∃</b> 3	Ė
			SC-73 (SOT223)	sym028



### 150 V, 1 A PNP high-voltage low VCEsat transistor

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package	ackage						
	Name	Description	Version					
PBHV9115Z-Q		plastic, surface-mounted package with increased heatsink; 4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body	SOT223					

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PBHV9115Z-Q	V9115Z

# 8. Limiting values

#### Table 5. Limiting values

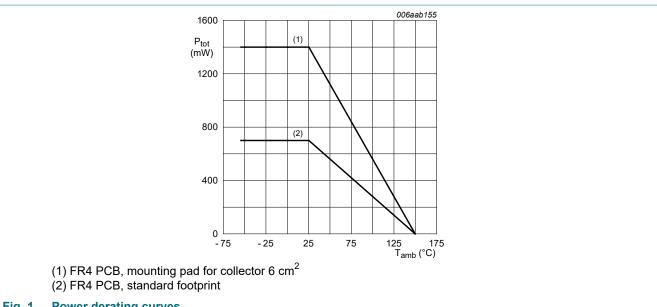
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-200	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-150	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-6	V
I <sub>C</sub>	collector current			-	-1	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-2	А
I <sub>BM</sub>	peak base current			-	-400	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	0.7	W
			[2]	-	1.4	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

### 150 V, 1 A PNP high-voltage low VCEsat transistor



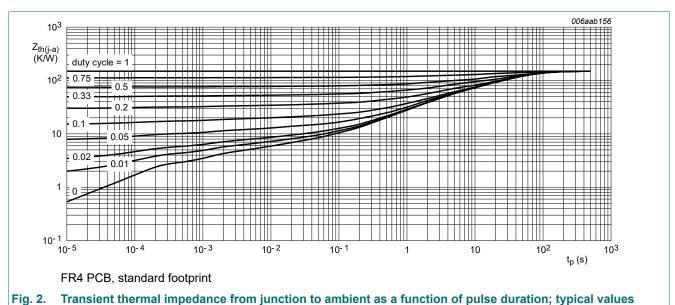
## Fig. 1. Power derating curves

### 9. Thermal characteristics

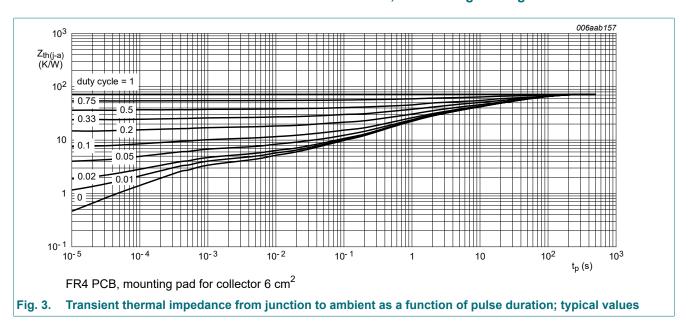
**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from	in free air	[1]	-	-	175	K/W
juno	junction to ambient		[2]	-	-	89	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



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## 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = -120 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	V <sub>CB</sub> = -120 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-10	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = -4 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = -120 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -10 V; I <sub>C</sub> = -50 mA; T <sub>amb</sub> = 25 °C	100	220	-	
		$V_{CE}$ = -10 V; $I_{C}$ = -100 mA; $T_{amb}$ = 25 °C	100	220	-	
		$V_{CE}$ = -10 V; $I_{C}$ = -1 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	10	30	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = -100 mA; $I_B$ = -10 mA; $T_{amb}$ = 25 °C	-	-60	-120	mV
		I <sub>C</sub> = -100 mA; I <sub>B</sub> = -20 mA; T <sub>amb</sub> = 25 °C	-	-50	-100	mV
		$I_{C}$ = 500 mA; $I_{B}$ = -100 mA; $T_{amb}$ = 25 °C	-	-150	-300	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C$ = -1 A; $I_B$ = -200 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-1.05	-1.2	V
t <sub>d</sub>	delay time	$V_{CC} = -6 \text{ V}; I_C = -0.5 \text{ A}; I_{Bon} = -0.1 \text{ A};$	-	8	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = 0.1 A; T <sub>amb</sub> = 25 °C	-	282	-	ns
t <sub>on</sub>	turn-on time		-	290	-	ns
t <sub>s</sub>	storage time		-	430	-	ns
t <sub>f</sub>	fall time		-	300	-	ns
t <sub>off</sub>	turn-off time		-	730	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = -10 V; $I_{C}$ = -10 mA; f = 100 MHz; $T_{amb}$ = 25 °C	-	115	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -20 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	10	-	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = -0.5 \text{ V}; I_C = 0 \text{ A}; i_c = 0 \text{ A}; f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	-	150	-	pF

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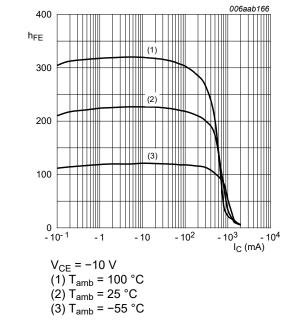


Fig. 4. DC current gain as a function of collector current; typical values

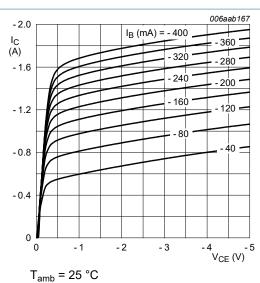
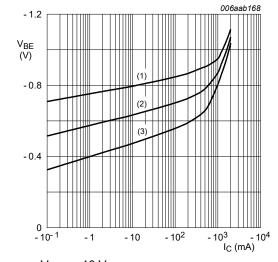


Fig. 5. Collector current as a function of collectoremitter voltage; typical values



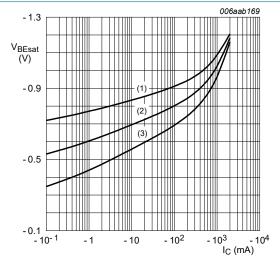
 $V_{CE} = -10 \text{ V}$ 

$$(1) T_{amb} = -55 °C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



$$I_C/I_B = 5$$

$$(1) T_{amb} = -55 °C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

#### 150 V, 1 A PNP high-voltage low VCEsat transistor

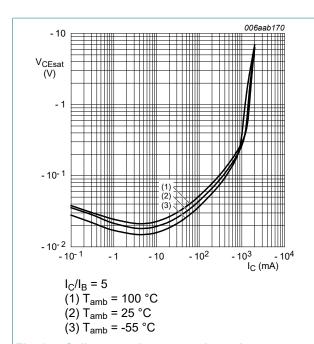


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

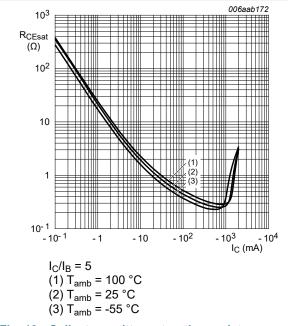


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

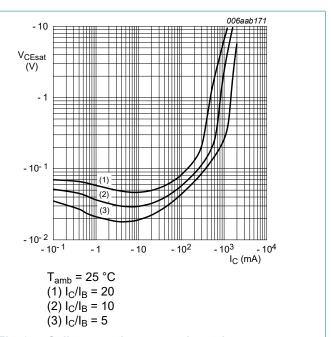


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

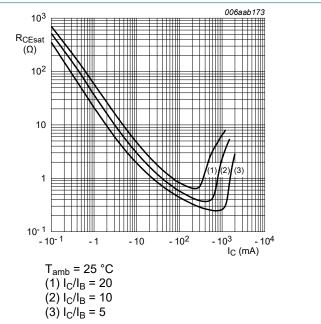
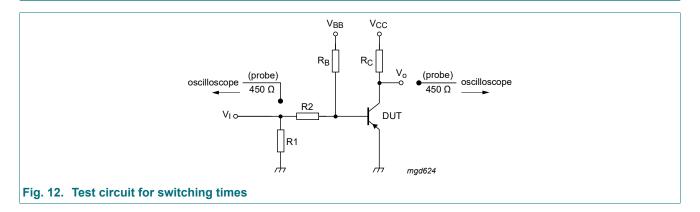


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

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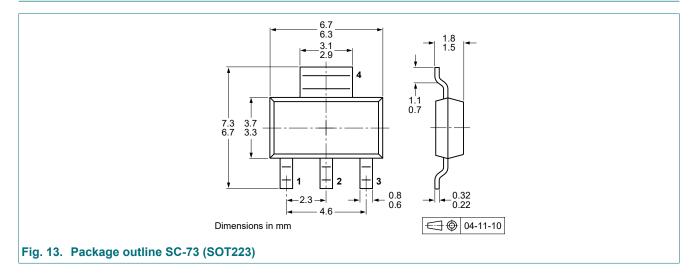
## 11. Test information



### **Quality information**

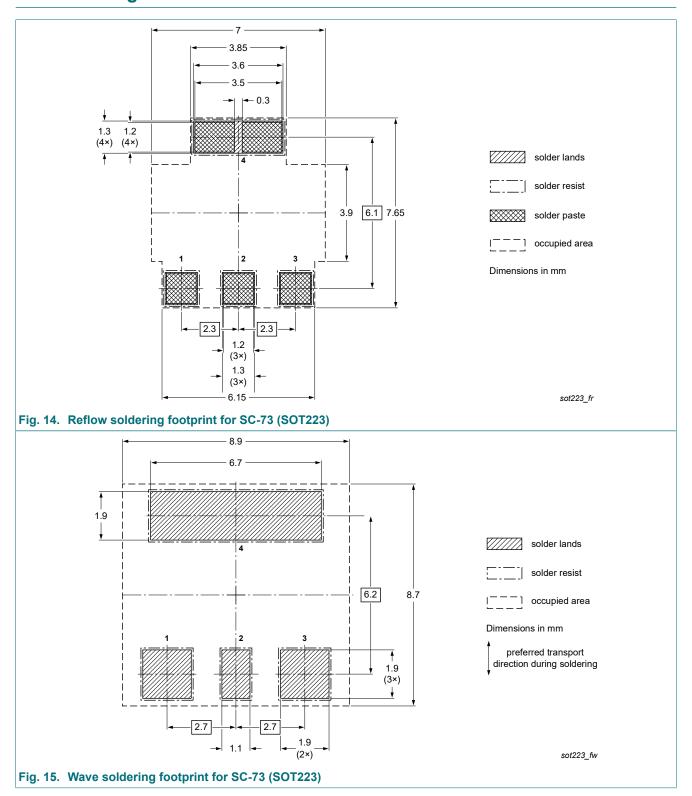
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

# 12. Package outline



### 150 V, 1 A PNP high-voltage low VCEsat transistor

# 13. Soldering



150 V, 1 A PNP high-voltage low VCEsat transistor

# 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV9115Z-Q v.1	20230717	Product data sheet	-	-

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PBHV9115Z-Q

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